MC100EP91

2.5 V/3.3 V Any Level Positive Input to -3.3 V/-5.5 V NECL Output Translator

ON Semiconductor®

Description

The MC100EP91 is a triple any level positive input to NECL output translator. The device accepts LVPECL, LVTTL, LVCMOS, HSTL, CML or LVDS signals, and translates them to differential NECL output signals (-3.0 V / -5.5 V).

To accomplish the level translation the EP91 requires three power rails. The V_{CC} pins should be connected to the positive power supply, and the V_{EE} pin should be connected to the negative power supply. The GND pins are connected to the system ground plane. Both V_{EE} and V_{CC} should be bypassed to ground via 0.01 µF capacitors.

Under open input conditions, the $\overline{D}$ input will be biased at $V_{CC}/2$ and the D input will be pulled to GND. These conditions will force the Q outputs to a low state, and $\overline{Q}$ outputs to a high state, which will ensure stability.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 µF capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.
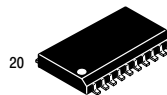
Features

- Maximum Input Clock Frequency > 2.0 GHz Typical
- Maximum Input Data Rate > 2.0 Gb/s Typical
- 500 ps Typical Propagation Delay
- Operating Range: V_{CC} = 2.375 V to 3.8 V;
  V_{EE} = -3.0 V to -5.5 V; GND = 0 V
- Q Output will Default LOW with Inputs Open or at GND
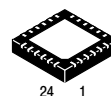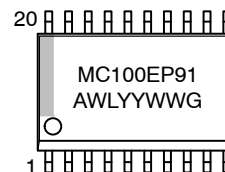- Pb−Free Packages are Available*

MARKING DIAGRAMS*

**SO−20 WB
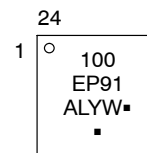DW SUFFIX
CASE 751D**

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MC100EP91
AWLYYWWG
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**24 PIN QFN
MN SUFFIX
CASE 485L**

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100
EP91
ALYW■
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A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G or ■	= Pb−Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.
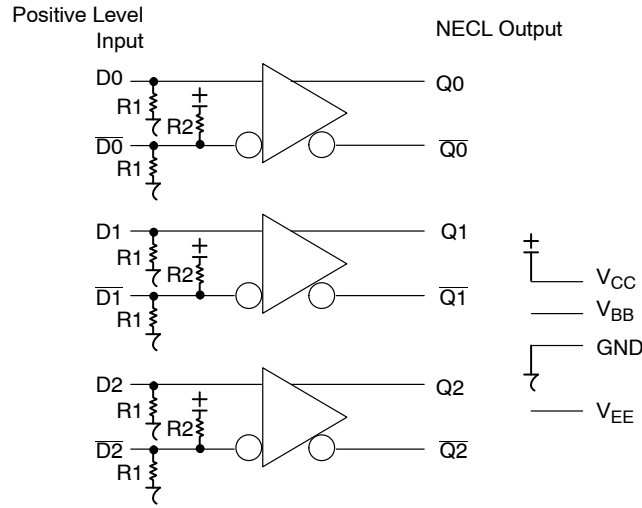
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Figure 1. Logic Diagram

Table 1. PIN DESCRIPTION

Pin		Name	I/O	Default State	Description
SOIC	**QFN**				
1, 20	3, 4, 12	V_{CC}	–	–	Positive Supply Voltage. All V_{CC} Pins must be Externally Connected to Power Supply to Guarantee Proper Operation.
10	15, 16	V_{EE}	–	–	Negative Supply Voltage. All V_{EE} Pins must be Externally Connected to Power Supply to Guarantee Proper Operation.
14, 17	19, 20, 23, 24	GND	–	–	Ground.
4, 7	7, 11	V_{BB}	–	–	ECL Reference Voltage Output
2, 5, 8	5, 8, 13	D[0:2]	LVPECL, LVDS, LVTTL, LVCMOS, CML, HSTL Input	Low	Noninverted Differential Inputs [0:2]. Internal 75 kΩ to GND.
3, 6, 9	6, 9, 14	$\overline{D}$[0:2]	LVPECL, LVDS, LVTTL,LVCMOS, CML, HSTL Input	High	Inverted Differential Inputs [0:2]. Internal 75 kΩ to GND and 75 kΩ to V_{CC}. When Inputs are Left Open They Default to (V_{CC} – GND) / 2.
19,16,13	2, 22, 18	Q[0:2]	NECL Output	–	Noninverted Differential Outputs [0:2]. Typically Terminated with 50 Ω to V_{TT} = V_{CC} – 2 V
18,15,12	1, 21, 17	$\overline{Q}$[0:2]	NECL Output	–	Inverted Differential Outputs [0:2]. Typically Terminated with 50 Ω to V_{TT} = V_{CC} – 2 V
11	10	NC	–	–	No Connect. The NC Pin is NOT Electrically Connected to the Die and may Safely be Connected to Any Voltage from V_{EE} to V_{CC}.
N/A	–	EP	–		Exposed Pad. (Note 1)

1. The thermally conductive exposed pad on the package bottom (see case drawing) must be attached to a heat−sinking conduit and may only be electrically connected to V_{EE} (not GND).
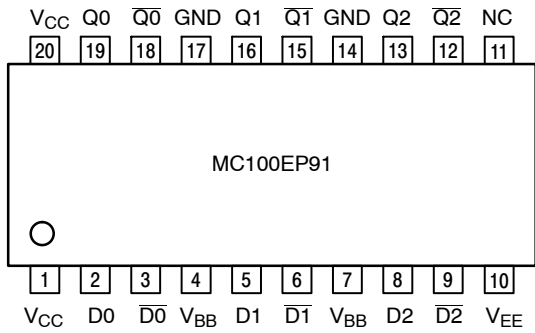
MC100EP91

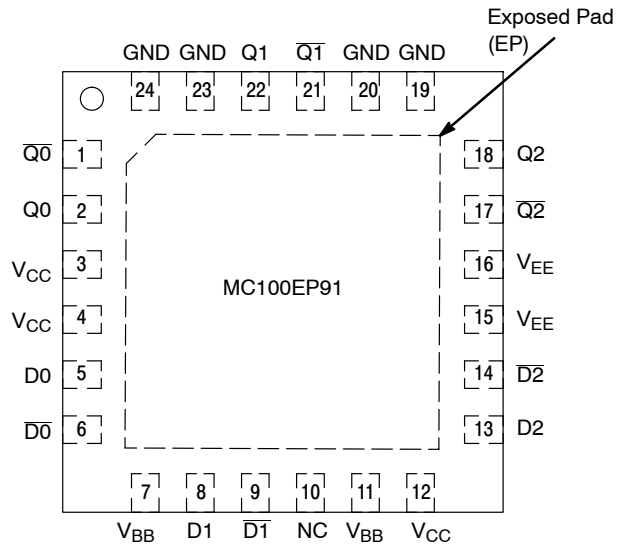**Figure 2. SOIC−20 Lead Pinout** (Top View)

Figure 3. QFN−24 Lead Pinout (Top View)*

*All V_{CC}, V_{EE} and GND pins must be externally connected to a power supply and the underside exposed pad must be attached to an adequate heat−sinking conduit to guarantee proper operation.

Table 2. ATTRIBUTES

Characteristics		Value	
Internal Input Pulldown Resistor	(R1)	75 kΩ	
Internal Input Pullup Resistor	(R2)	75 kΩ	
ESD Protection	Human Body Model Machine Model Charged Device Model	> 2 kV > 150 V > 2 kV	
Moisture Sensitivity (Note 2)		Pb Pkg	Pb−Free Pkg
	SO−20 WB QFN−24	Level 1 Level 1	Level 3 Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
Transistor Count		446 Devices	
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test			

2. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Positive Power Supply	GND = 0 V		3.8 to 0	V
V_{EE}	Negative Power Supply	GND = 0 V		−6	V
V_I	Positive Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	3.8 to 0	V
V_{OP}	Operating Voltage	GND = 0 V	$V_{CC} - V_{EE}$	9.8	V
I_{out}	Output Current	Continuous Surge		50 100	mA mA
I_{BB}	PECL V_{BB} Sink/Source			± 0.5	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction−to−Ambient) JESD 51−3 (1S−Single Layer Test Board)	0 lfpm 500 lfpm	SOIC−20 SOIC−20	90 60	°C/W °C/W
θ_{JA}	Thermal Resistance (Junction−to−Ambient) JESD 51−6 (2S2P Multilayer Test Board) with Filled Thermal Vias	0 lfpm 500 lfpm	QFN−24 QFN−24	37 32	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	SOIC−20 QFN−24	30 to 35 11	°C/W °C/W
T_{sol}	Wave Solder Pb Pb−Free			225 225	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 4. DC CHARACTERISTICS POSITIVE INPUTS V_{CC} = 2.5 V, V_{EE} = −3.0 V to −5.5 V, GND = 0 V (Note 3)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{CC}	Positive Power Supply Current	10	14	20	10	14	20	10	14	20	mA
V_{IH}	Input HIGH Voltage (Single−Ended)	1335		V_{CC}	1335		V_{CC}	1335		V_{CC}	mV
V_{IL}	Input LOW Voltage (Single−Ended)	GND		875	GND		875	GND		875	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	0		2.5	0		2.5	0		2.5	V
I_{IH}	Input HIGH Current (@ V_{IH})			150			150			150	μA
I_{IL}	Input LOW Current (@ V_{IL}) D $\overline{D}$	0.5 −150			0.5 −150			0.5 −150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

3. Input parameters vary 1:1 with V_{CC}. V_{CC} can vary +1.3 V / −0.125 V.
4. V_{IHCMR} min varies 1:1 with GND. V_{IHCMR} max varies 1:1 with V_{CC}.

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Table 5. DC CHARACTERISTICS POSITIVE INPUT V_{CC} = 3.3 V; V_{EE} = −3.0 V to −5.5 V; GND = 0 V (Note 5)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{CC}	Positive Power Supply Current	10	16	24	10	16	24	10	16	24	mA
V_{IH}	Input HIGH Voltage (Single−Ended)	2135		V_{CC}	2135		V_{CC}	2135		V_{CC}	mV
V_{IL}	Input LOW Voltage (Single−Ended)	GND		1675	GND		1675	GND		1675	mV
V_{BB}	PECL Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 6)	0		3.3	0		3.3	0		3.3	V
I_{IH}	Input HIGH Current (@ V_{IH})			150			150			150	μA
I_{IL}	Input LOW Current (@ V_{IL}) D / $\overline{D}$	0.5 / −150			0.5 / −150			0.5 / −150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

5. Input parameters vary 1:1 with V_{CC}. V_{CC} can vary +0.5 / −0.925 V.
6. V_{IHCMR} min varies 1:1 with GND. V_{IHCMR} max varies 1:1 with V_{CC}.

Table 6. DC CHARACTERISTICS NECL OUTPUT V_{CC} = 2.375 V to 3.8 V; V_{EE} = −3.0 V to −5.5 V; GND = 0 V (Note 7)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Negative Power Supply Current	40	50	60	38	50	68	38	50	68	mA
V_{OH}	Output HIGH Voltage (Note 8)	−1145	−1020	−895	−1145	−1020	−895	−1145	−1020	−895	mV
V_{OL}	Output LOW Voltage (Note 8)	−1945	−1770	−1600	−1945	−1770	−1600	−1945	−1770	−1600	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

7. Output parameters vary 1:1 with GND.
8. All loading with 50 Ω resistor to GND − 2.0 V.

Table 7. AC CHARACTERISTICS V_{CC} = 2.375 V to 3.8 V; V_{EE} = −3.0 V to −5.5 V; GND = 0 V

Symbol	Characteristic		−40°C			25°C			85°C			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{OUTPP}	Output Voltage Amplitude (Figure 4) (Note 9)	$f_{in} \leq$ 1.0 GHz $f_{in} \leq$ 1.5 GHz $f_{in} \leq$ 2.0 GHz	575 525 300	800 750 600		600 525 250	800 750 550		550 400 150	800 750 500		mV
t_{PLH} t_{PHL0}	Propagation Delay D to Q	Differential Single−Ended	375 300	500 450	600 650	375 300	500 450	600 675	400 300	550 500	650 750	ps
t_{SKEW}	Pulse Skew (Note 10) Output−to−Output (Note 11) Part−to−Part (Diff) (Note 11)			15 25 50	75 95 125		15 30 50	75 105 125		15 30 70	80 105 150	ps
t_{JITTER}	RMS Random Clock Jitter (Note 12) Peak−to−Peak Data Dependant Jitter (Note 13)	f_{in} = 2.0 GHz f_{in} = 2.0 Gb/s		0.5 20	2.0		0.5 20	2.0		0.5 20	2.0	ps
V_{INPP}	Input Voltage Swing (Differential Configuration) (Note 14)		200	800	1200	200	800	1200	200	800	1200	mV
t_r, t_f	Output Rise/Fall Times @ 50 MHz (20% − 80%)	Q, $\overline{Q}$	75	150	250	75	150	250	75	150	275	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

9. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to GND − 2.0 V. Input edge rates 150 ps (20% − 80%).
10. Pulse Skew = |t_{PLH} − t_{PHL}|
11. Skews are valid across specified voltage range, part−to−part skew is for a given temperature.
12. RMS Jitter with 50% Duty Cycle Input Clock Signal.
13. Peak−to−Peak Jitter with input NRZ PRBS $2^{31−1}$ at 2.0 Gb/s.
14. Input voltage swing is a single−ended measurement operating in differential mode. The device has a DC gain of ≈ 50.
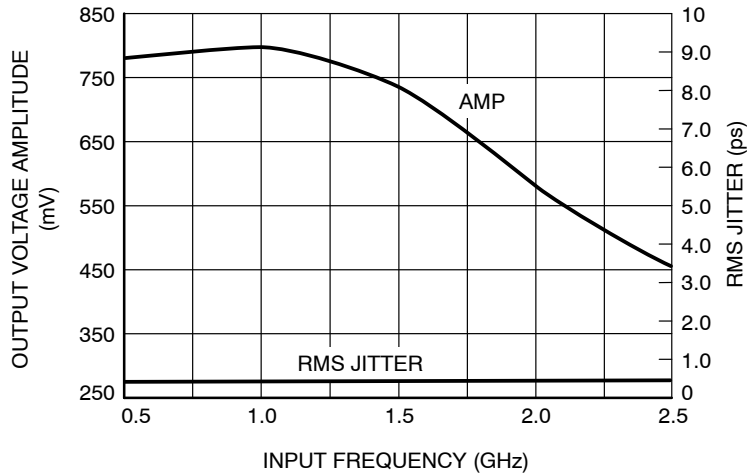
Figure 4. Output Voltage Amplitude (V_{OUTPP}) / RMS Jitter vs. Input Frequency (f_{in}) at Ambient Temperature (Typical)
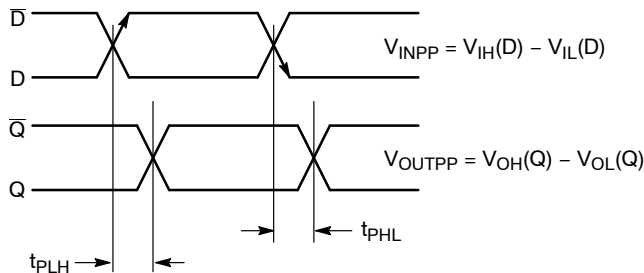
Figure 5. AC Reference Measurement

Application Information

All MC100EP91 inputs can accept LVPECL, LVTTL, LVCMOS, HSTL, CML, or LVDS signal levels. The limitations for differential input signal (LVDS, HSTL, LVPECL, or CML) are the minimum input swing of 150 mV and the maximum input swing of 3.0 V. Within these conditions, the input voltage can range from V_{CC} to GND. Examples interfaces are illustrated below in a 50 Ω environment (Z = 50 Ω)
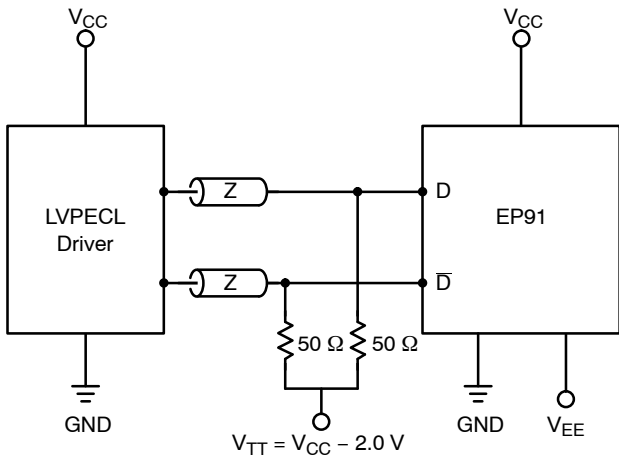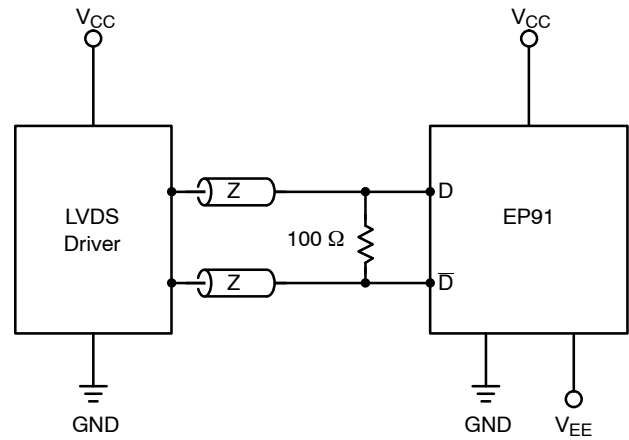
Figure 6. Standard LVPECL Interface

Figure 7. Standard LVDS Interface
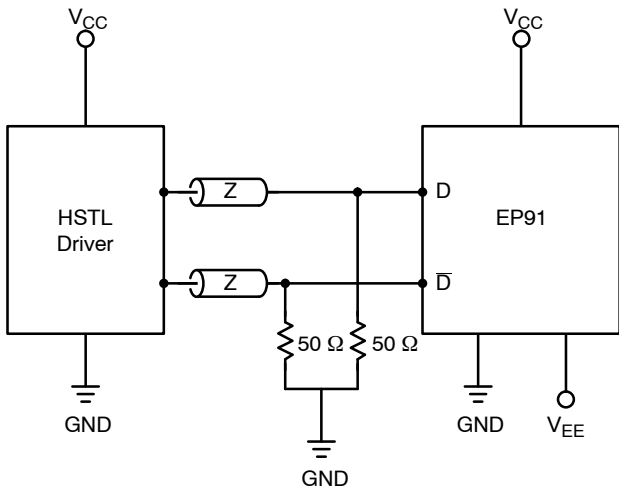
Figure 8. Standard HSTL Interface
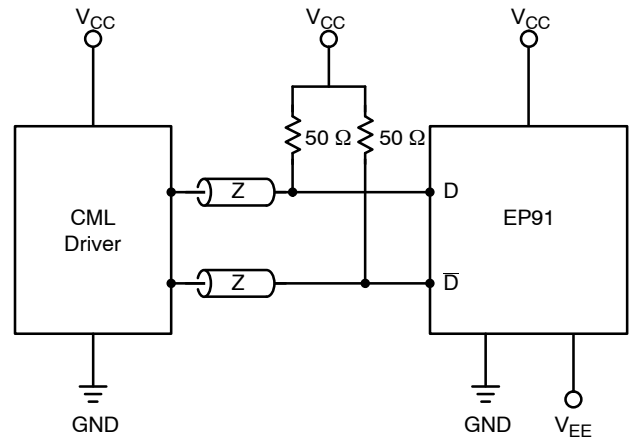
Figure 9. Standard 50 Ω Load CML Interface
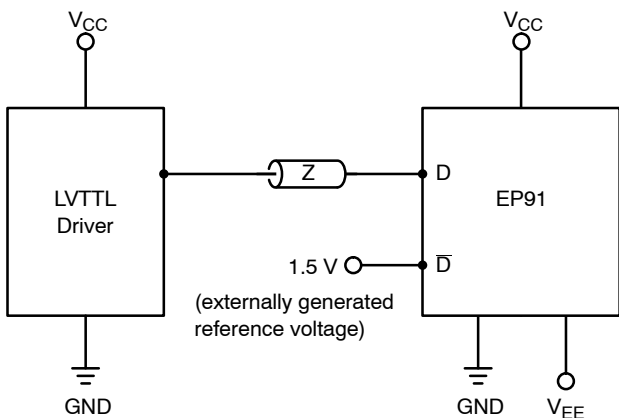
Figure 10. Standard LVTTL Interface
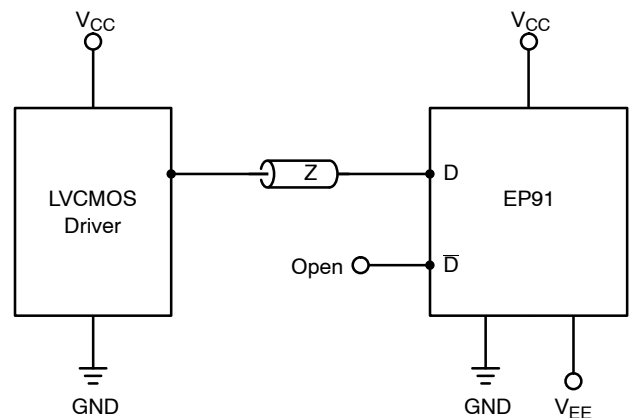
Figure 11. Standard LVCMOS Interface
($\overline{D}$ will default to $V_{CC}/2$ when left open.
A reference voltage of $V_{CC}/2$ should be applied
to D input, if $\overline{D}$ is interfaced to CMOS signals.)

ORDERING INFORMATION

Device	Package	Shipping†
MC100EP91DW	SO−20	38 Units / Rail
MC100EP91DWG	SO−20 (Pb−Free)	38 Units / Rail
MC100EP91DWR2	SO−20	1000 / Tape & Reel
MC100EP91DWR2G	SO−20 (Pb−Free)	1000 / Tape & Reel
MC100EP91MN	QFN−24	92 Units / Rail
MC100EP91MNG	QFN−24 (Pb−Free)	92 Units / Rail
MC100EP91MNR2	QFN−24	3000 / Tape & Reel
MC100EP91MNR2G	QFN−24 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
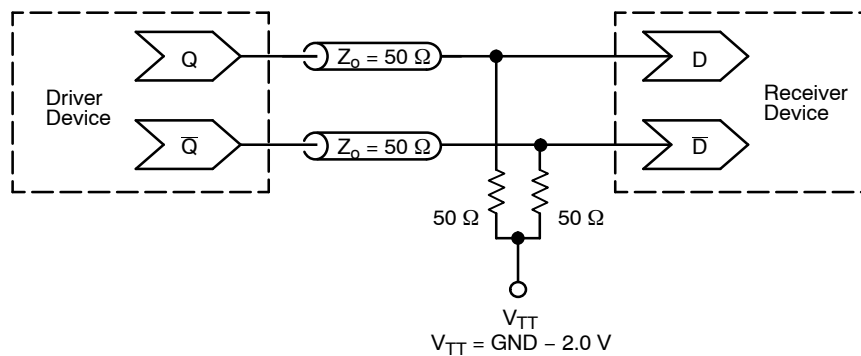
**Figure 12. Typical Termination for Output Driver and Device Evaluation
(See Application Note AND8020/D – Termination of ECL Logic Devices.)**

Resource Reference of Application Notes

AN1405/D – ECL Clock Distribution Techniques

AN1406/D – Designing with PECL (ECL at +5.0 V)

AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D – Metastability and the ECLinPS Family

AN1568/D – Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8002/D – Marking and Date Codes

AND8020/D – Termination of ECL Logic Devices

AND8066/D – Interfacing with ECLinPS

AND8090/D – AC Characteristics of ECL Devices

MC100EP91

PACKAGE DIMENSIONS

SO−20 WB
CASE 751D−05
ISSUE G
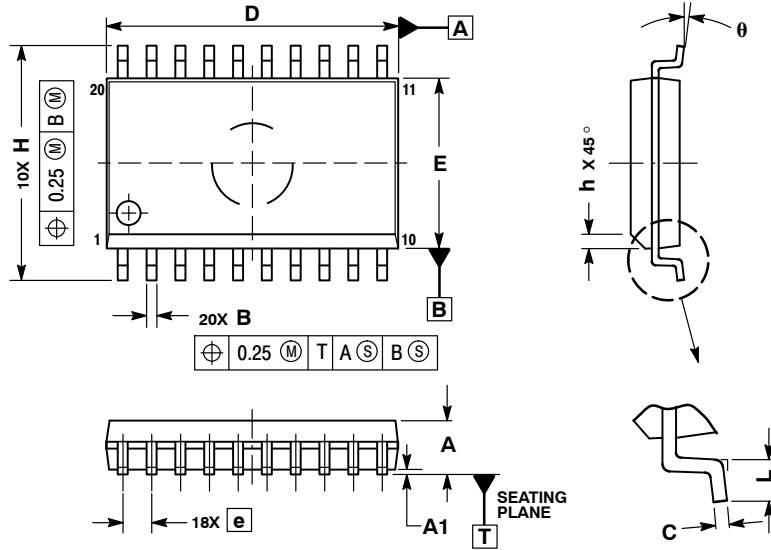
NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

PACKAGE DIMENSIONS

QFN 24
MN SUFFIX
24 PIN QFN, 4x4
CASE 485L
ISSUE A
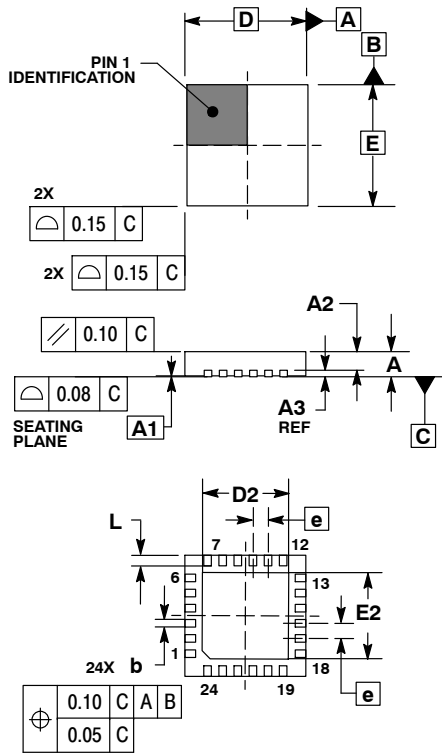
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A2	0.60	0.80
A3	0.20 REF	
b	0.20	0.30
D	4.00 BSC	
D2	2.70	2.90
E	4.00 BSC	
E2	2.70	2.90
e	0.50 BSC	
L	0.30	0.50

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